Abstracts

Measurement of dynamic load lines of power heterojunction bipolar transistor

S. Ohara, Y. Nakasha, T. Iwai and K. Joshin. "Measurement of dynamic load lines of power heterojunction bipolar transistor." 1997 MTT-S International Microwave Symposium Digest 2. (1997 Vol. II [MWSYM]): 909-912.

Dynamic load lines of InGaP/GaAs Heterojunction Bipolar Transistors (HBTs) were experimentally measured with a load circuit tuned to maximum collector efficiency (/spl eta//sub c/) and maximum gain. The phase relationship between the collector voltage and the collector current depended on the load circuit. The trajectory of the dynamic load line has a non-oval shape for the output power where gain compression heavily occurs.

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